

FIG.1

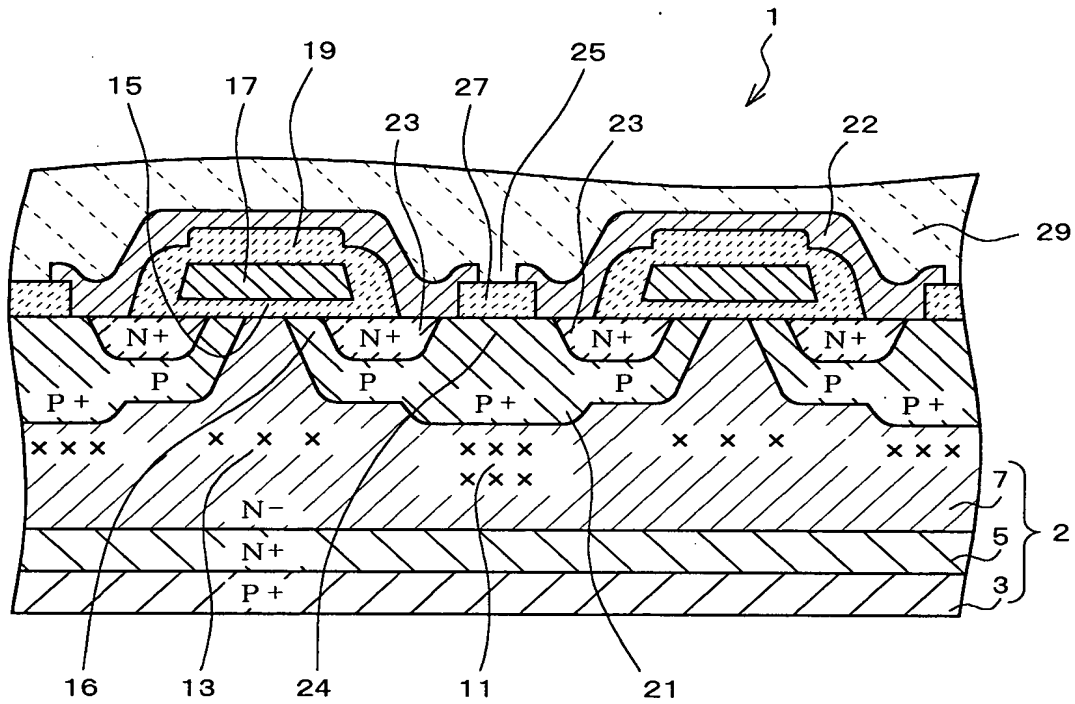


FIG.2

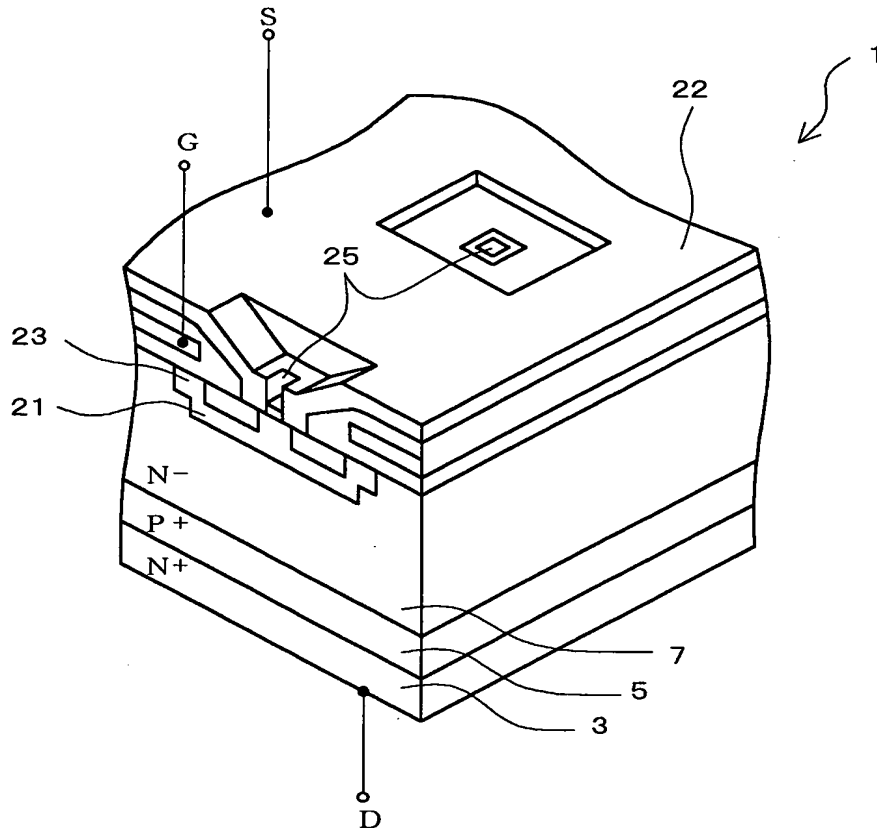


FIG.3

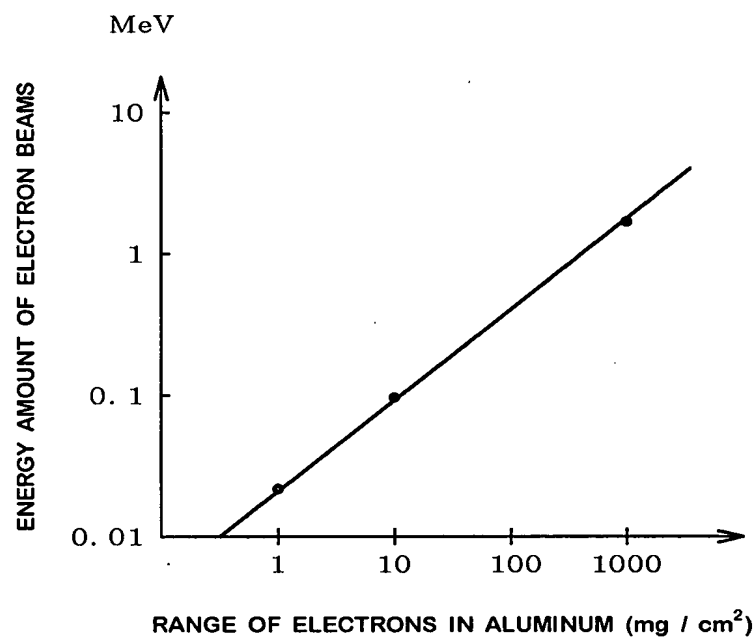


FIG.4A

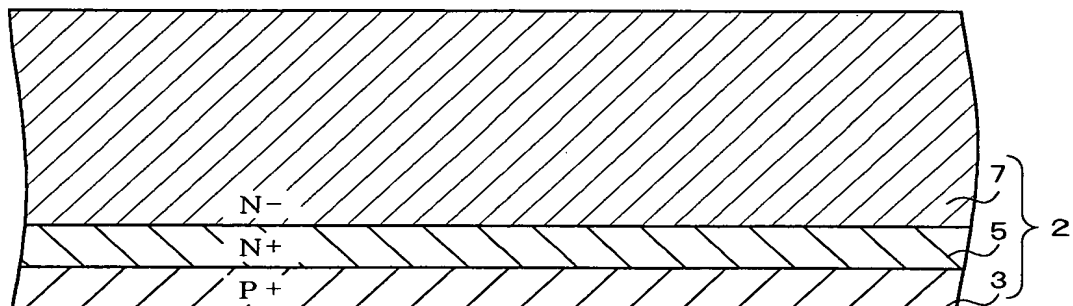


FIG.4B

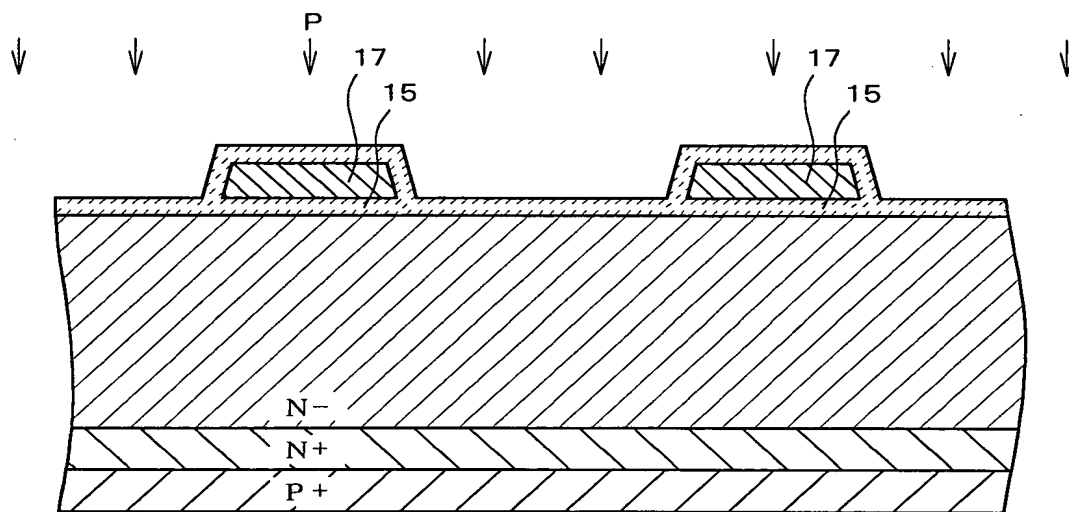
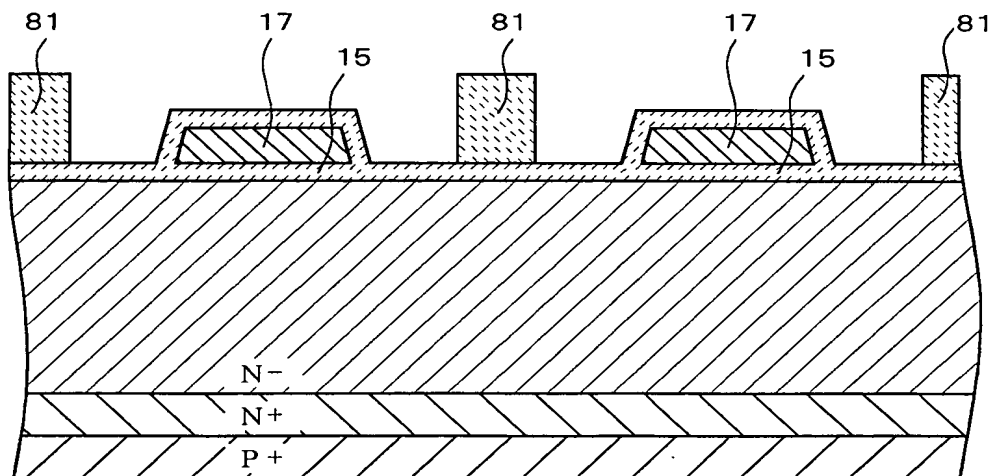


FIG.4C



**FIG. 5B**

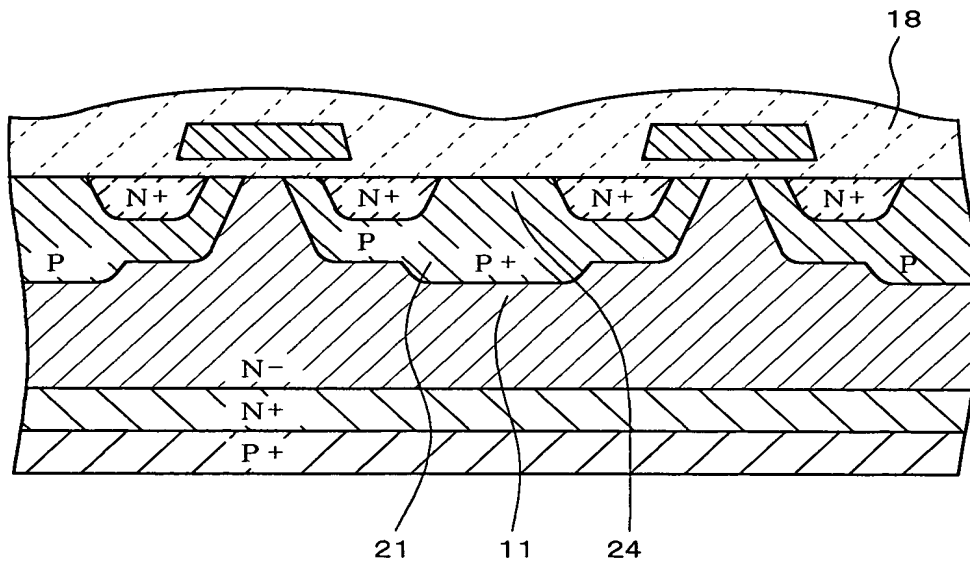


FIG.6A

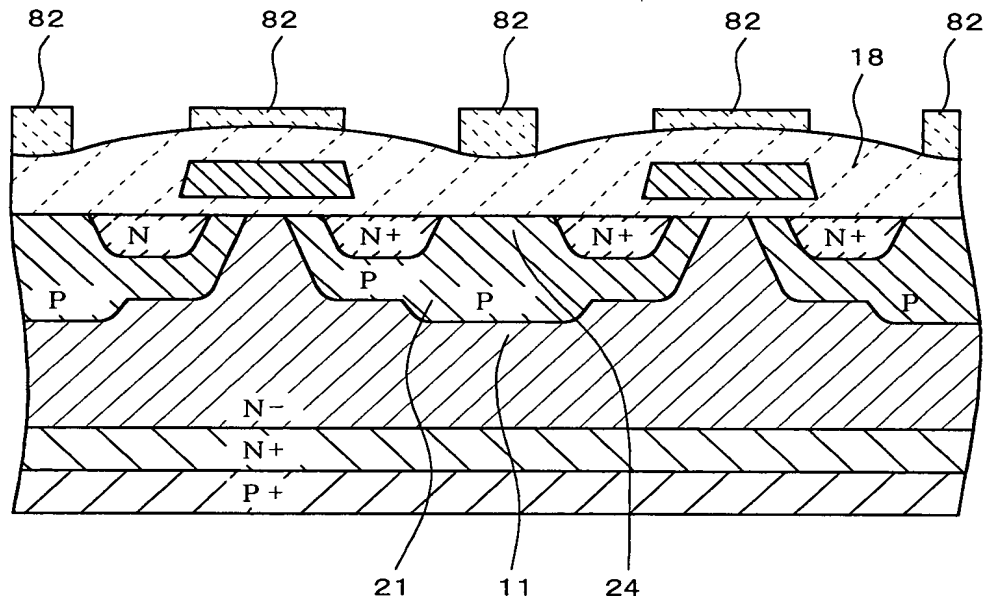


FIG.6B

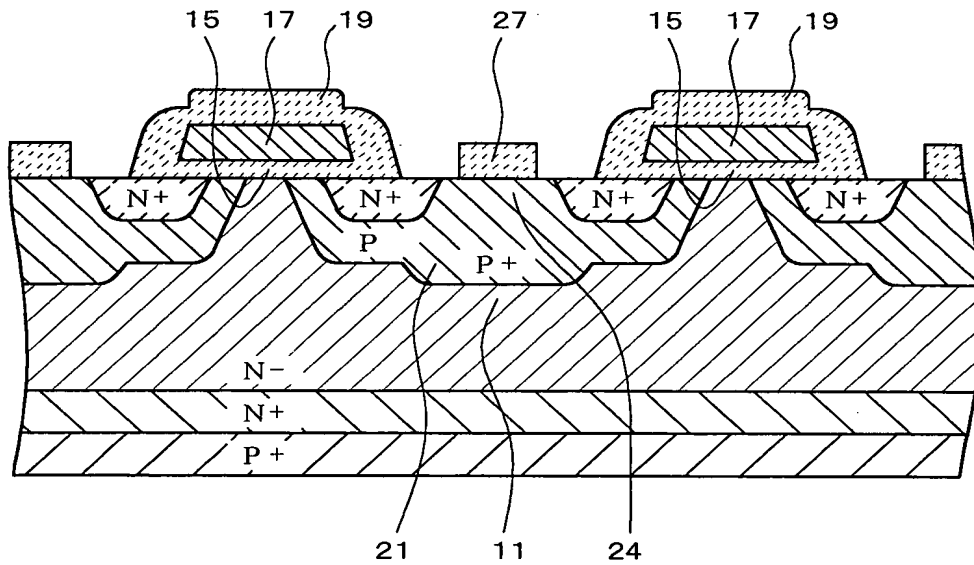


FIG.7A

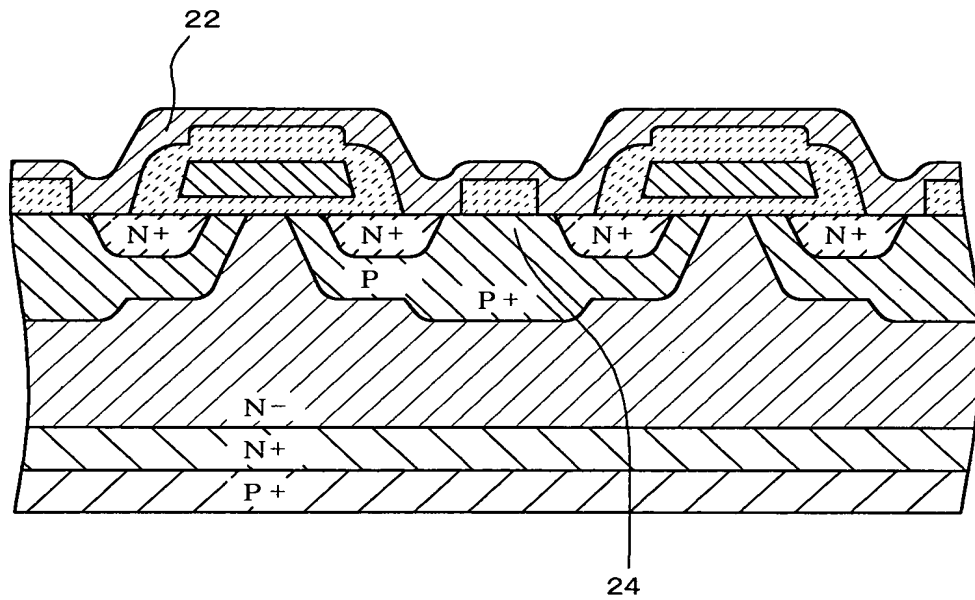
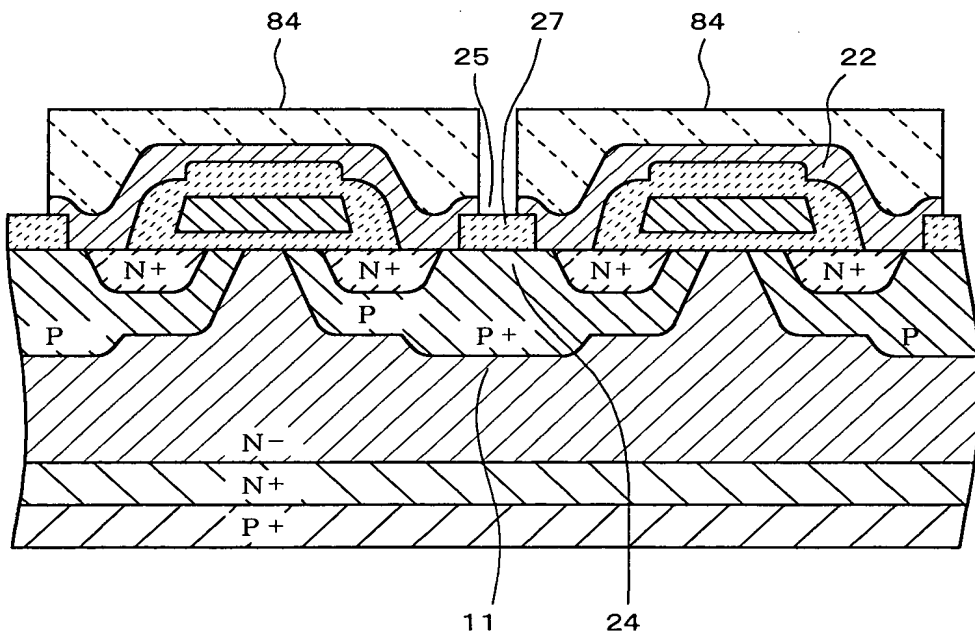


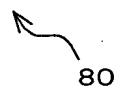
FIG.7B



A cross-sectional view of a semiconductor device 11. The device consists of a substrate with multiple layers: an N+ layer, a P layer, and a P+ layer. The P+ layer is the bottom-most layer. Above it is a P layer, which contains several N+ regions. The top layer is labeled 22 and has a complex, wavy profile. Two specific features on the top layer are labeled 25 and 27. Arrows at the top of the diagram indicate incident light or a signal.



**<PRIOR ART>**



**<PRIOR ART>**

